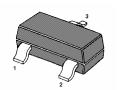
Silicon Epitaxial Planar Schottky Barrier Diode





Marking Code: "XY" SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit	
Reverse Voltage	V _R	30	V	
Forward Current (Single)		30	mA	
Forward Current (Double)	IF	20	IIIA	
Peak Forward Current (Single)		150	mA	
Peak Forward Current (Double)	I _{FM}	110		
Junction Temperature	T _j	125	°C	
Storage Temperature Range	T _{stg}	- 55 to + 125	°C	

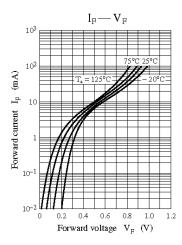
Characteristics at T_a = 25 °C

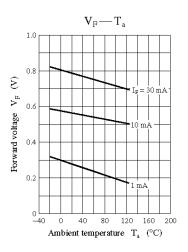
Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 30 \text{ mA}$	V _F	-	0.4 1	V
Reverse Current at V _R = 30 V	I _R	-	1	μΑ
Terminal Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$	C _t	2.7	-	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{rr} = 1$ mA, $R_L = 100$ Ω	t _{rr}	1	-	ns

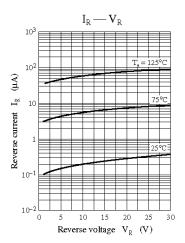


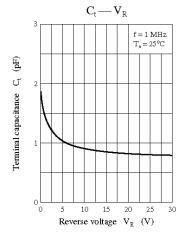


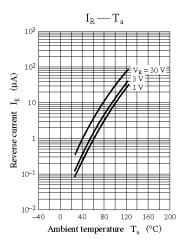
















(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 28/04/2007